



60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D Tc = +25°C
60V	16mΩ @ V _{GS} = 10V	37.1A
80 V	24mΩ @ V _{GS} = 4.5V	30.3A

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- < 1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH6016LPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

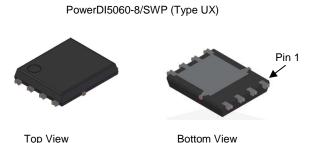
Description and Applications

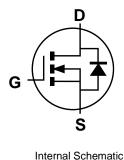
This MOSFET has been designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

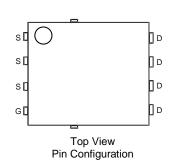
- Power management
- DC-DC converters
- Motor controls

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- · Weight: 0.097 grams (Approximate)







Ordering Information (Note 4)

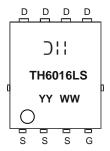
Part Number	Package	Packing		
Fait Number	Package	Qty.	Carrier	
DMTH6016LPSWQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



TH6016LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 23 = 2023) WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	60	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$			ID	37.1 26.2	А
Continuous Drain Current (Note 6) V _{GS} = 10V Steady State T _A = +25° T _A = +100			I _D	10.6 7.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	145	Α
Maximum Continuous Body Diode Forward Current (Note 5)			Is	31	Α
Avalanche Current, L = 0.1mH			I _{AS}	15.3	Α
Avalanche Energy, L = 0.1mH			Eas	11.7	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	49	°C/W
Total Power Dissipation (Note 5)	Tc = +25°C	PD	37.5	W
Thermal Resistance, Junction to Case (Note 5)		Rejc	4	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Notes:

^{5.} Thermal resistance from junction to soldering point (on the exposed drain pad).6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

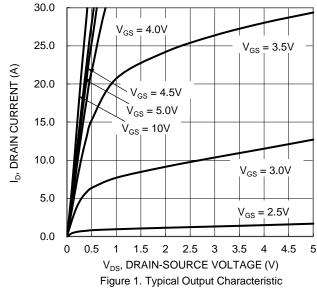
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	60	_	_	V	Vgs = 0V, ID = 250µA	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(th)	1	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	12.4	16	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	18.2	24	11177	$V_{GS} = 4.5V, I_D = 18A$	
Diode Forward Voltage	VsD	_	0.7	1.2	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	864	_		V _{DS} = 30V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	282	_	pF		
Reverse Transfer Capacitance	Crss	_	27	_			
Gate Resistance	Rg	_	1.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	8.4	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	17	_	nC	V _{DS} = 30V, I _D = 10A	
Gate-Source Charge	Qgs	_	3.1	_	nc		
Gate-Drain Charge	Q_{gd}	_	4.3	_			
Turn-On Delay Time	td(on)	_	3.4	_		$V_{GS} = 10V, V_{DS} = 30V$ $R_{G} = 6\Omega, I_{D} = 10A$	
Turn-On Rise Time	t _R	_	5.2	_	20		
Turn-Off Delay Time	tD(OFF)	_	13	_	ns		
Turn-Off Fall Time	t _F	_	7	_			
Reverse Recovery Time	trr	_	22	_	ns	I 400 dl/dt 4000/	
Reverse Recovery Charge	Qrr	_	11	_	nC	IF = 10A, dI/dt = 100A/μs	

Notes:

^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







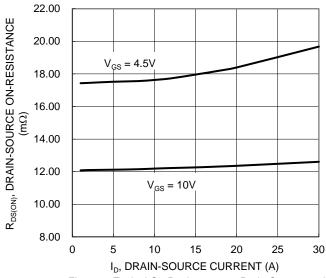


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

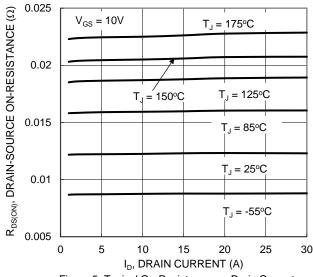
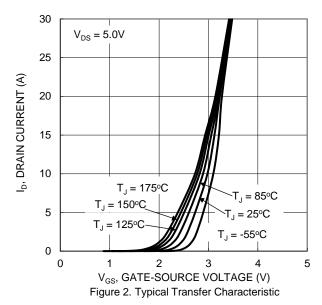
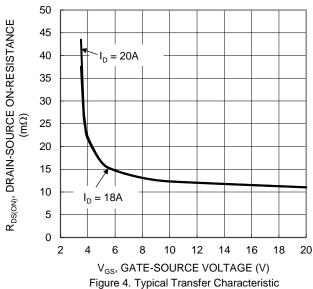


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





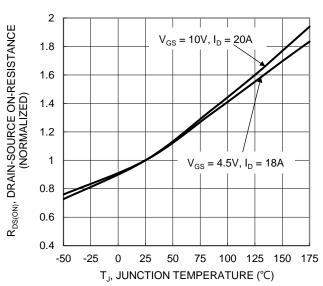


Figure 6. On-Resistance Variation with Temperature





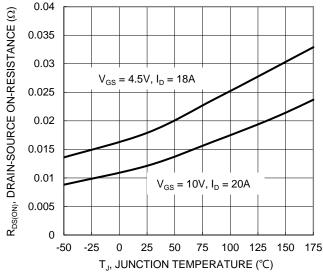
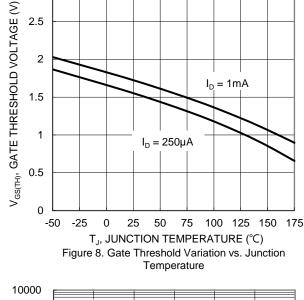
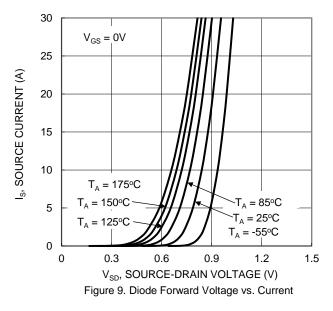
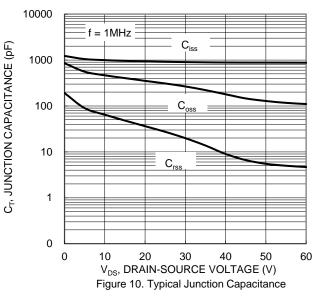


Figure 7. On-Resistance Variation with Temperature



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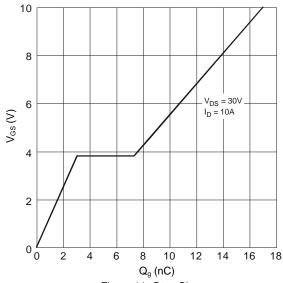
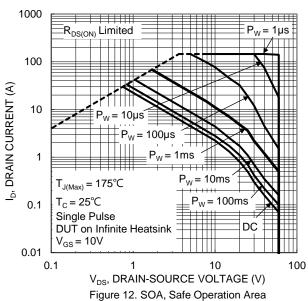


Figure 11. Gate Charge



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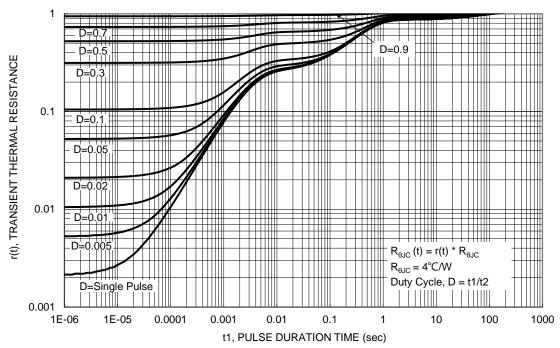


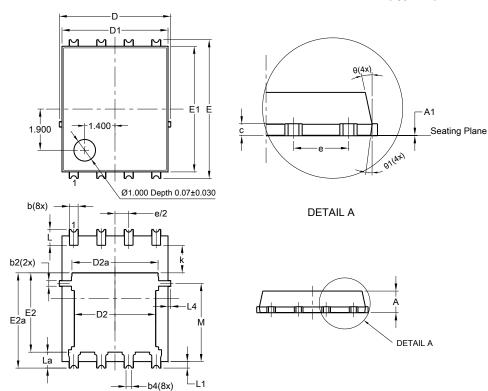
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)

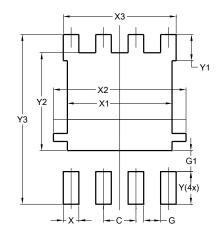


Ро	PowerDI5060-8/SWP (Type UX)				
Dim	Min Max Typ				
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF			
C D	0.230	0.330	0.277		
	5	.15 BS0)		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78 4.18 3.98				
Е	6	.40 BS0)		
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е		.27BSC)		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	5.190		
Х3	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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